











TSV911, TSV912, TSV914

SBOS878D-JULY 2017-REVISED OCTOBER 2019

TSV91x Rail-to-Rail Input/Output, 8-MHz Operational Amplifiers

Features

Rail-to-rail input and output

Low noise: 18 nV/√Hz at 1 kHz

Low power consumption: 550 µA (typical)

High-gain bandwidth: 8 MHz

Operating supply voltage from 2.5 V to 5.5 V

Low input bias current: 1 pA (typical)

Low input offset voltage: 1.5 mV (maximum)

Low offset voltage drift: ±0.5 µV/°C (typical)

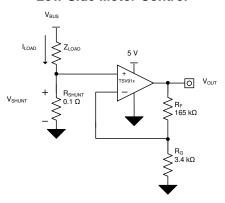
ESD internal protection: ±4-kV human-body model

Extended temperature range: -40°C to 125°C

Applications

- Battery-powered applications
- Motor control
- Power modules
- HVAC: heating, ventilating, and air conditioning
- Washing machines
- Refrigerators
- Medical instrumentation
- Active filters
- Sensor signal conditioning
- Audio receiver
- Automotive infotainment

Low-Side Motor Control



3 Description

The TSV91x family, which includes single-, dual-, and quad-channel operational amplifiers (op amps), is for specifically designed general-purpose applications. Featuring rail-to-rail input and output (RRIO) swings, wide bandwidth (8 MHz), and low offset voltage (0.3 mV, typical), this family is designed for a variety of applications that require a good balance between speed and power consumption. The op amps are unity-gain stable and feature an ultralow input bias current, which enables the family to be used in applications with high-source impedances. The low input bias current allows the devices to be used for sensor interfaces, battery-supplied and portable applications, and active filtering.

The robust design of the TSV91x provides ease-ofuse to the circuit designer. Features include a unitygain stable, integrated RFI-EMI rejection filter, no phase reversal in overdrive condition, and high electrostatic discharge (ESD) protection (4-kV HBV).

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TC\/044	SOT-23 (5)	1.60 mm × 2.90 mm
TSV911	SC70 (5)	1.25 mm × 2.00 mm
	SOIC (8)	3.91 mm × 4.90 mm
TSV912	WSON (8)	2.00 mm × 2.00 mm
	SOT-23 (8)	1.60 mm × 2.90 mm
TC\/04.4	SOIC (14)	8.65 mm × 3.91 mm
TSV914	TSSOP (14)	4.40 mm × 5.00 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Small-Signal Overshoot vs Load Capacitance

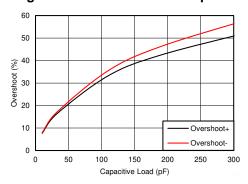




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Changes from Revision A (October 2017) to Revision B

Page

Deleted package preview note from TSV912 DSG package pinout drawing in Pin Configuration and Functions section 6 Changed TSV914 PW (TSSOP) junction-to-ambient thermal resistance from 135.8°C/W to 205.8°C/W9 Changed TSV914 PW (TSSOP) junction-to-case(top) thermal resistance from 64°C/W to 106.7°C/W......9

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Changed TSV914 PW (TSSOP) junction-to-board thermal resistance from 79°C/W to 133.9°C/W.....9

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•	Changed TSV914 PW (TSSOP) junction-to-top characterization parameter from 15.7°C/W to 34.4°C/W	<u>9</u>
<u>.</u>	Changed TSV914 PW (TSSOP) junction-to-board characterization parameter from 78.4°C/W to 132.6°C/W	9
Cr	hanges from Original (July 2017) to Revision A	Page
•	Changed TSV914 14-pin SOIC package from preview to production data in <i>Device Information</i> table	1
•	Deleted TSV911 SC70, SOT-553 and SOIC packages from Device Information table	1
•	Deleted TSV912 VSSOP packages from Device Information table	1
•	Deleted TSV911 SC70 and SOIC packages from pinout drawings and <i>Pin Functions</i> table	5
•	Deleted TSV912 DGK and DGS packages from pinout images Pin Functions table	6
•	Deleted package preview note from TSV914 pinout drawing and Pin Functions table	7
•	Added TSV914 Thermal Information table	9
	Added 2017 copyright notice to Figure 35.	



5 Device Comparison Table

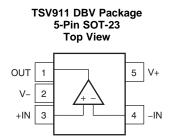
DEVICE	NO. OF			PACKAGI	E LEADS		
DEVICE	CHANNELS	DBV	DCK	D	DSG	PW	DDF
TSV911	1	5	5	_	_	_	_
TSV912	2	_	_	8	8	_	8
TS\/01/	1	_		1/		1/	

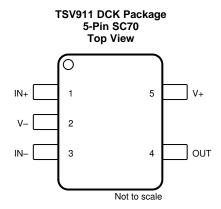
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6 Pin Configuration and Functions



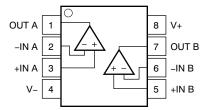


Pin Functions: TSV911

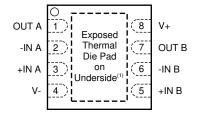
	PIN			
NAME	NO. DBV (SOT-23) DCK (SC70)		I/O	DESCRIPTION
NAIVIE				
-IN	4	3	ı	Inverting input
+IN	3	1	ı	Noninverting input
OUT	1	4	0	Output
V-	2	2	_	Negative (lowest) supply or ground (for single-supply operation)
V+	5	5	_	Positive (highest) supply



TSV912 D, DGK, DDF Packages 8-Pin SOIC, VSSOP Top View



TSV912 DSG Package (1) 8-Pin WSON With Exposed Thermal Pad Top View



 Connect exposed thermal pad to V-. See Packages with an Exposed Thermal Pad section for more information.

Pin Functions: TSV912

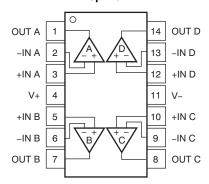
PIN		1/0	DESCRIPTION	
NAME	NO.	1/0	DESCRIPTION	
–IN A	2	I	Inverting input, channel A	
+IN A	3	I	Noninverting input, channel A	
–IN B	6	I	Inverting input, channel B	
+IN B	5	I	Noninverting input, channel B	
OUT A	1	0	Output, channel A	
OUT B	7	0	Output, channel B	
V-	4	_	Negative (lowest) supply or ground (for single-supply operation)	
V+	8	_	Positive (highest) supply	

Product Folder Links: TSV911 TSV912 TSV914

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TSV914 D, PW Packages 14-Pin SOIC, TSSOP Top View



Pin Functions: TSV914

PIN		1/0	DESCRIPTION
NAME	NO.	1/0	DESCRIPTION
–IN A	2	I	Inverting input, channel A
+IN A	3	1	Noninverting input, channel A
–IN B	6	1	Inverting input, channel B
+IN B	5	I	Noninverting input, channel B
–IN C	9	I	Inverting input, channel C
+IN C	10	1	Noninverting input, channel C
–IN D	13	1	Inverting input, channel D
+IN D	12	1	Noninverting input, channel D
OUT A	1	0	Output, channel A
OUT B	7	0	Output, channel B
OUT C	8	0	Output, channel C
OUT D	14	0	Output, channel D
V-	11	_	Negative (lowest) supply or ground (for single-supply operation)
V+	4	_	Positive (highest) supply



7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature (unless otherwise noted) (1)

			MIN	MAX	UNIT	
Supply voltage				6	V	
Signal input pins	Voltage ⁽²⁾	Common-mode	(V-) - 0.5	(V+) + 0.5	V	
	Voltage (=/	Differential		(V+) - (V-) + 0.2	V	
	Current ⁽²⁾		-10	10	mA	
Output short-circuit	(3)		Conti	Continuous		
Specified, T _A		-40	125	°C		
Junction, T _J			150	°C		
Storage, T _{stg}			-65	150	°C	

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 ESD Ratings

over operating free-air temperature range (unless otherwise noted)

			VALUE	UNIT
V	Floatroatotic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±4000	V
V _(ESD) Electro	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	±1500	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	MAX	UNIT
V _S Supply voltage	2.5	5.5	V
Specified temperature	-40	125	°C

7.4 Thermal Information: TSV911

		TSV		
	THERMAL METRIC ⁽¹⁾	DBV (SOT-23)	DCK (SC70)	UNIT
		5 PINS	5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	221.7	263.3	°C/W
$R_{\theta JC(top)}$	Junction-to-case(top) thermal resistance	144.7	75.5	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	49.7	51.0	°C/W
ΨЈТ	Junction-to-top characterization parameter	26.1	1.0	°C/W
ΨЈВ	Junction-to-board characterization parameter	49.0	50.3	°C/W

 For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

⁽²⁾ Input pins are diode-clamped to the power-supply rails. Current limit input signals that can swing more than 0.5 V beyond the supply rails to 10 mA or less.

⁽³⁾ Short-circuit to ground, one amplifier per package.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



7.5 Thermal Information: TSV912

		TSV912				
	THERMAL METRIC ⁽¹⁾	D (SOIC)	DGK (VSSOP)	DSG (WSON)	DDF (SOT-23)	UNIT
		8 PINS	8 PINS	8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	157.6	201.2	94.4	184.4	°C/W
$R_{\theta JC(top)}$	Junction-to-case(top) thermal resistance	104.6	85.7	116.5	112.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	99.7	122.9	61.3	99.9	°C/W
ΨЈТ	Junction-to-top characterization parameter	55.6	21.2	13	18.7	°C/W
ΨЈВ	Junction-to-board characterization parameter	99.2	121.4	61.7	99.3	°C/W
R _{θJC(bot)}	Junction-to-case(bottom) thermal resistance	N/A	N/A	34.4	N/A	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

7.6 Thermal Information: TSV914

			TSV914				
	THERMAL METRIC ⁽¹⁾	D (SOIC)	PW (TSSOP)	UNIT			
		14 PINS	14 PINS				
$R_{\theta JA}$	Junction-to-ambient thermal resistance	106.9	205.8	°C/W			
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	69	106.7	°C/W			
$R_{\theta JB}$	Junction-to-board thermal resistance	63	133.9	°C/W			
ΨЈТ	Junction-to-top characterization parameter	25.9	34.4	°C/W			
ΨЈВ	Junction-to-board characterization parameter	62.7	132.6	°C/W			

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.



7.7 Electrical Characteristics: V_s (Total Supply Voltage) = (V+) - (V-) = 2.5 V to 5.5 V

at $T_A = 25^{\circ}$ C, $R_L = 10 \text{ k}\Omega$ connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{OUT} = V_S / 2$ (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFFSET	VOLTAGE						
		V _S = 5 V		±0.3	±1.5		
V _{OS}	Input offset voltage	V _S = 5 V T _A = -40°C to 125°C			±3	mV	
dV _{OS} /dT	Drift	$V_S = 5 V$ $T_A = -40$ °C to 125°C		±0.5		μV/°C	
PSRR	Power-supply rejection ratio	$V_S = 2.5 \text{ V} - 5.5 \text{ V}, V_{CM} = (V-)$		±7		μV/V	
	Channel separation, DC	At DC		100		dB	
NPUT V	OLTAGE RANGE				·		
V _{CM}	Common-mode voltage range	V _S = 2.5 V to 5.5 V	(V-) - 0.1		(V+) + 0.1	V	
		$V_S = 5.5 \text{ V}$ $(V-) - 0.1 \text{ V} < V_{CM} < (V+) - 1.4 \text{ V}$ $T_A = -40^{\circ}\text{C}$ to 125°C	80	103			
CMRR	Common-mode rejection ratio	$V_S = 5.5 \text{ V}, V_{CM} = -0.1 \text{ V to } 5.6 \text{ V}$ $T_A = -40^{\circ}\text{C to } 125^{\circ}\text{C}$	57	87		dB	
	,	$V_S = 2.5 \text{ V}, (V-) - 0.1 \text{ V} < V_{CM} < (V+) - 1.4 \text{ V}$ $T_A = -40^{\circ}\text{C}$ to 125°C		88			
		V _S = 2.5 V, V _{CM} = -0.1 V to 1.9 V T _A = -40°C to 125°C		81			
NPUT B	IAS CURRENT		•		+		
I _B	Input bias current			±1		pA	
los	Input offset current			±0.05		pА	
NOISE			"				
= n	Input voltage noise (peak-to-peak)	$V_S = 5 \text{ V}, f = 0.1 \text{ Hz to } 10 \text{ Hz}$		4.77		μV _{PP}	
		$V_S = 5 \text{ V, f} = 10 \text{ kHz}$		12			
e _n	Input voltage noise density	$V_S = 5 \text{ V, f} = 1 \text{ kHz}$		18		nV/√Hz	
i _n	Input current noise density	f = 1 kHz		10		fA/√Hz	
	APACITANCE						
C _{ID}	Differential			2		pF	
C _{IC}	Common-mode			4		pF	
	OOP GAIN			•		Ρ.	
		$V_S = 2.5 \text{ V}, (V-) + 0.04 \text{ V} < V_O < (V+) - 0.04 \text{ V}$ $R_L = 10 \text{ k}\Omega$		100			
		$V_S = 5.5 \text{ V}, (V-) + 0.05 \text{ V} < V_O < (V+) - 0.05 \text{ V}$ $R_L = 10 \text{ k}\Omega$	104	130			
A _{OL}	Open-loop voltage gain	$V_S = 2.5 \text{ V}, (V-) + 0.06 \text{ V} < V_O < (V+) - 0.06 \text{ V}$ $R_L = 2 \text{ k}\Omega$		100		dB	
		$V_S = 5.5 \text{ V}, (V-) + 0.15 \text{ V} < V_O < (V+) - 0.15 \text{ V}$ $R_L = 2 \text{ k}\Omega$		130			
FREQUE	NCY RESPONSE						
GBP	Gain bandwidth product	V _S = 5 V, G = 1		8		MHz	
Pm	Phase margin	V _S = 5 V, G = 1		55		۰	
SR	Slew rate	$\begin{array}{l} V_S=5~V,~G=1\\ R_L=2~k\Omega\\ C_L=100~pF \end{array}$		4.5		V/µs	
	Cottling time	To 0.1%, $V_S = 5 \text{ V}$, 2-V step , $G = 1$ $C_L = 100 \text{ pF}$		0.5		110	
İs	Settling time	To 0.01%, $V_S = 5 \text{ V}$, 2-V step , $G = 1$ $C_L = 100 \text{ pF}$		1		μs	
OR	Overload recovery time	$V_S = 5 \text{ V}, V_{IN} \times \text{gain} > V_S$		0.2		μs	
THD + N	Total harmonic distortion + noise ⁽¹⁾	V _S = 5 V, V _O = 1 V _{RMS} , G = 1, f = 1 kHz		0.0008%			
OUTPUT			*		"		
,	Voltage output swing from supply	$V_{S} = 5.5 \text{ V}, R_{L} = 10 \text{ k}\Omega$			15		
/ ₀	rails	$V_S = 5.5 \text{ V}, R_L = 2 \text{ k}\Omega$			50	mV	

Product Folder Links: TSV911 TSV912 TSV914

Third-order filter; bandwidth = 80 kHz at −3 dB. (1)

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Electrical Characteristics: V_S (Total Supply Voltage) = (V+) - (V-) = 2.5 V to 5.5 V (continued)

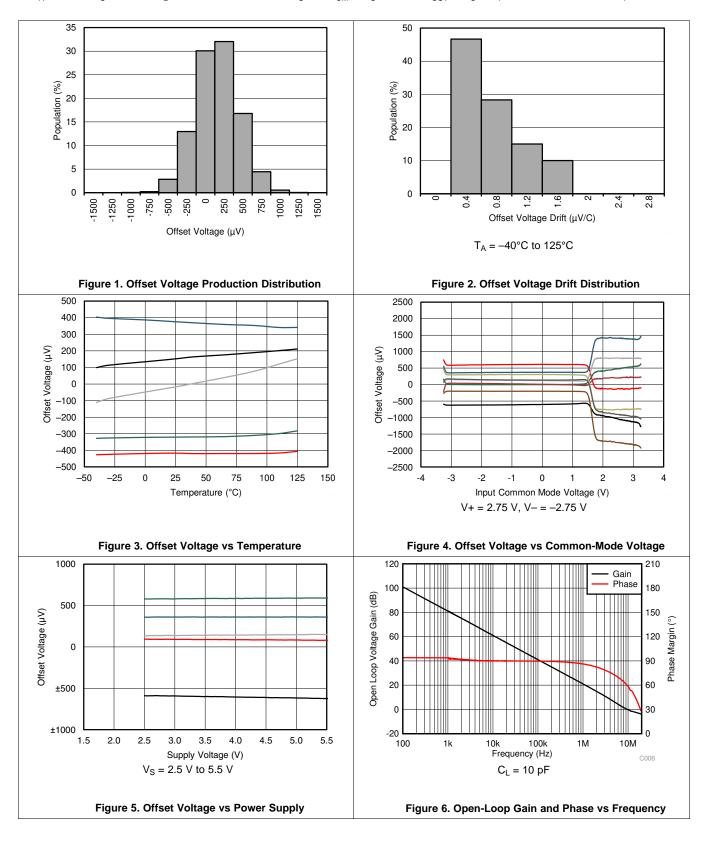
at $T_A = 25$ °C, $R_L = 10$ k Ω connected to V_S / 2, $V_{CM} = V_S$ / 2, and $V_{OUT} = V_S$ / 2 (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT			
I _{SC}	Short-circuit current	V _S = 5 V		±50		mA			
Z _O	Open-loop output impedance	V _S = 5 V, f = 10 MHz		100		Ω			
POWE	POWER SUPPLY								
	0	V _S = 5.5 V, I _O = 0 mA		550	750				
IQ	Quiescent current per amplifier	$V_{\rm S} = 5.5 \; {\rm V}, \; {\rm I}_{\rm O} = 0 \; {\rm mA} \; {\rm T}_{\rm A} = -40 {\rm ^{\circ}C} \; {\rm to} \; 125 {\rm ^{\circ}C}$			1100	μΑ			



7.8 Typical Characteristics

at T_A = 25°C, V_S = 5.5 V, R_L = 10 k Ω connected to V_S / 2, V_{CM} = V_S / 2, and V_{OUT} = V_S / 2 (unless otherwise noted)

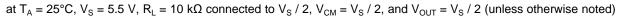


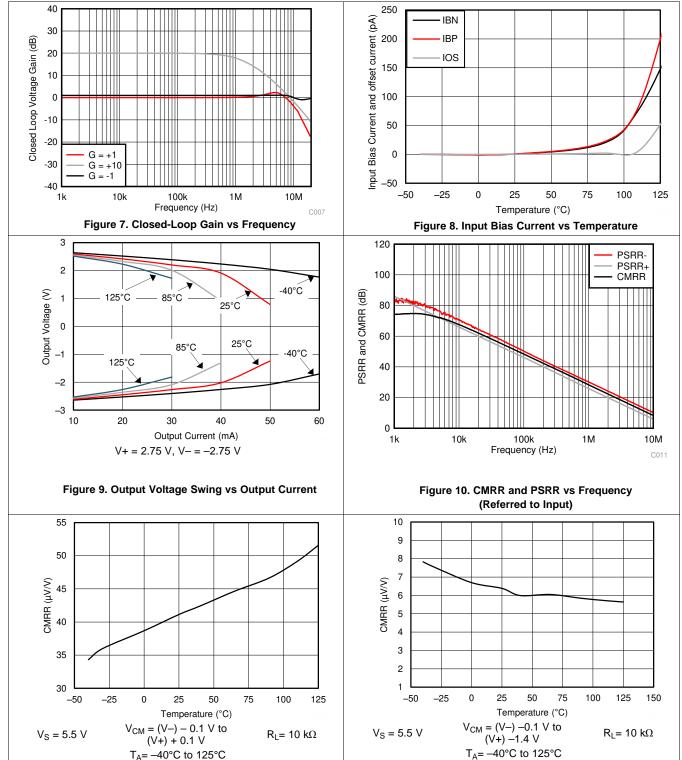
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Typical Characteristics (continued)





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Figure 11. CMRR vs Temperature

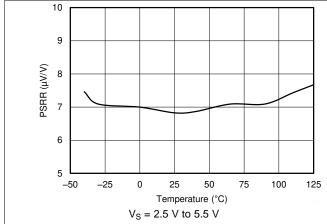
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Figure 12. CMRR vs Temperature

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Typical Characteristics (continued)

at $T_A = 25$ °C, $V_S = 5.5$ V, $R_L = 10$ k Ω connected to V_S / 2, $V_{CM} = V_S$ / 2, and $V_{OUT} = V_S$ / 2 (unless otherwise noted)



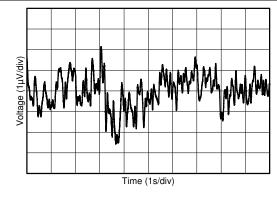
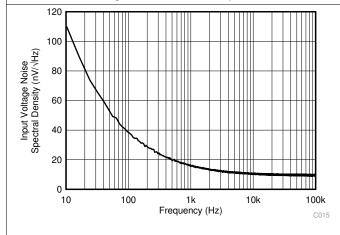


Figure 13. PSRR vs Temperature

Figure 14. 0.1-Hz to 10-Hz Input Voltage Noise

 $V_S = 2.5 \text{ V to } 5.5 \text{ V}$



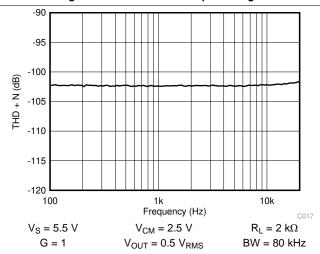
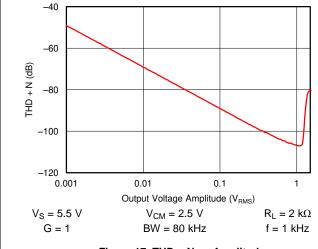


Figure 15. Input Voltage Noise Spectral Density vs Frequency

Figure 16. THD + N vs Frequency



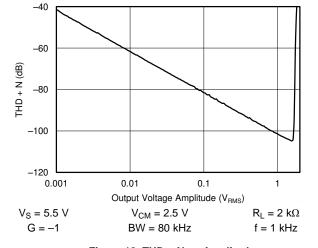
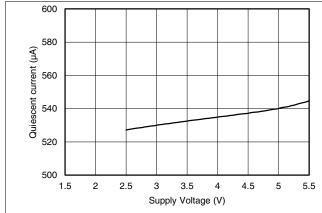


Figure 17. THD + N vs Amplitude Figure 18. THD + N vs Amplitude



Typical Characteristics (continued)

at $T_A = 25$ °C, $V_S = 5.5$ V, $R_L = 10$ k Ω connected to V_S / 2, $V_{CM} = V_S$ / 2, and $V_{OUT} = V_S$ / 2 (unless otherwise noted)



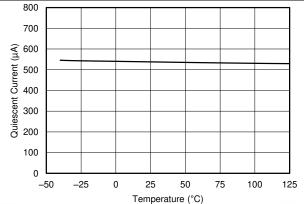
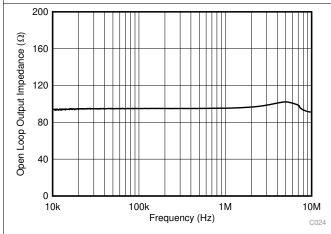


Figure 19. Quiescent Current vs Supply Voltage

Figure 20. Quiescent Current vs Temperature



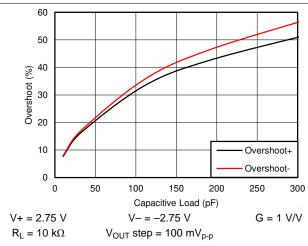
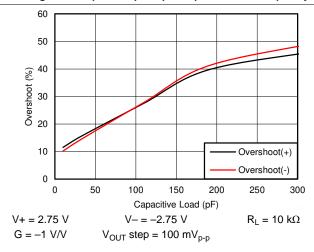


Figure 21. Open-Loop Output Impedance vs Frequency

Figure 22. Small-Signal Overshoot vs Load Capacitance



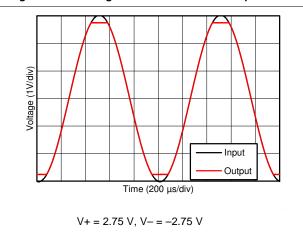


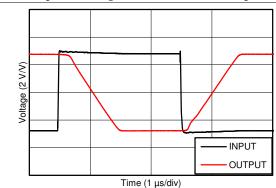
Figure 24. No Phase Reversal

Figure 23. Small-Signal Overshoot vs Load Capacitance

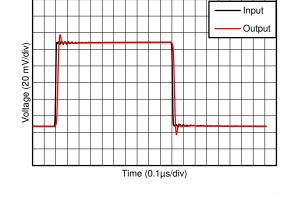
STRUMENTS

Typical Characteristics (continued)

at $T_A = 25$ °C, $V_S = 5.5$ V, $R_L = 10$ k Ω connected to V_S / 2, $V_{CM} = V_S$ / 2, and $V_{OUT} = V_S$ / 2 (unless otherwise noted)

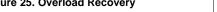


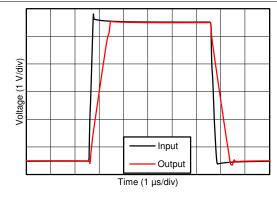
$$V+ = 2.75 V, V- = -2.75 V, G = -10 V/V$$



$$V+ = 2.75 V, V- = -2.75 V, G = 1 V/V$$

Figure 25. Overload Recovery





$$V- = -2.75 V$$

 $C_{L} = 100 \text{ pF}$

Figure 26. Small-Signal Step Response

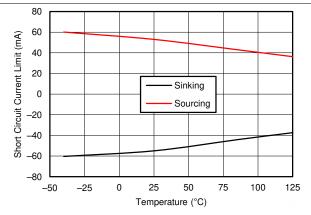


Figure 27. Large-Signal Step Response

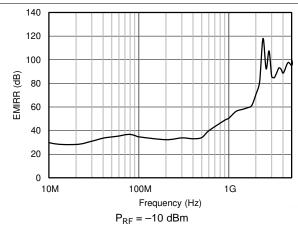
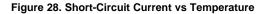


Figure 29. Electromagnetic Interference Rejection Ratio Referred to Noninverting Input (EMIRR+) vs Frequency



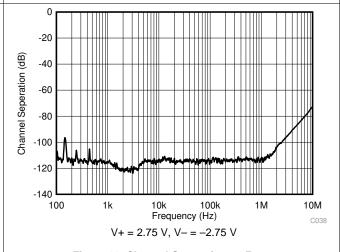
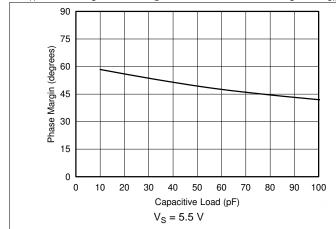


Figure 30. Channel Separation vs Frequency



Typical Characteristics (continued)

at $T_A = 25$ °C, $V_S = 5.5$ V, $R_L = 10$ k Ω connected to V_S / 2, $V_{CM} = V_S$ / 2, and $V_{OUT} = V_S$ / 2 (unless otherwise noted)



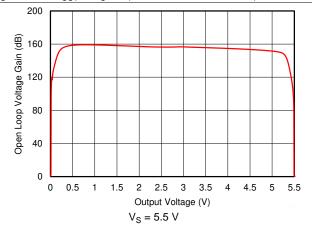
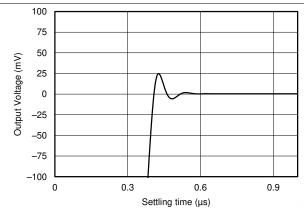


Figure 31. Phase Margin vs Capacitive Load





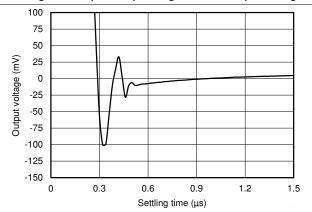


Figure 33. Large Signal Settling Time (Positive)

Figure 34. Large Signal Settling Time (Negative)

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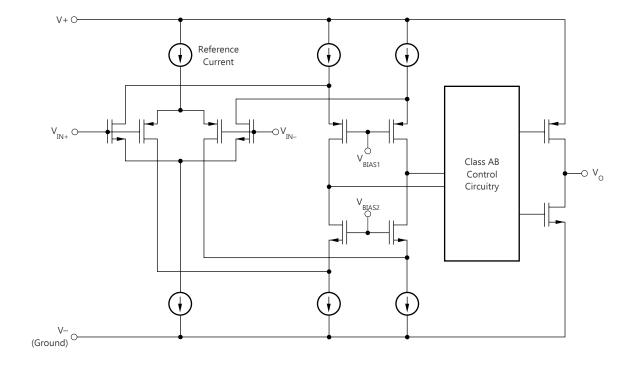


8 Detailed Description

8.1 Overview

The TSV91x series is a family of low-power, rail-to-rail input and output op amps. These devices operate from 2.5 V to 5.5 V, are unity-gain stable, and are designed for a wide range of general-purpose applications. The input common-mode voltage range includes both rails and allows the TSV91x series to be used in virtually any single-supply application. Rail-to-rail input and output swing significantly increases dynamic range, especially in low-supply applications and are designed for driving sampling analog-to-digital converters (ADCs).

8.2 Functional Block Diagram



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8.3 Feature Description

8.3.1 Rail-to-Rail Input

The input common-mode voltage range of the TSV91x family extends 100 mV beyond the supply rails for the full supply voltage range of 2.5 V to 5.5 V. This performance is achieved with a complementary input stage: an N-channel input differential pair in parallel with a P-channel differential pair, as shown in the *Functional Block Diagram*. The N-channel pair is active for input voltages close to the positive rail, typically (V+) - 1.4 V to 100 mV above the positive supply, whereas the P-channel pair is active for inputs from 100 mV below the negative supply to approximately (V+) - 1.4 V. There is a small transition region, typically (V+) - 1.2 V to (V+) - 1 V, in which both pairs are on. This 200-mV transition region can vary up to 200 mV with process variation. Thus, the transition region (with both stages on) can range from (V+) - 1.4 V to (V+) - 1.2 V on the low end, and up to (V+) - 1 V to (V+) - 0.8 V on the high end. Within this transition region, PSRR, CMRR, offset voltage, offset drift, and THD can degrade compared to device operation outside this region.

8.3.2 Rail-to-Rail Output

Designed as a low-power, low-voltage operational amplifier, the TSV91x series delivers a robust output drive capability. A class AB output stage with common-source transistors achieves full rail-to-rail output swing capability. For resistive loads of 10 k Ω , the output swings to within 15 mV of either supply rail, regardless of the applied power-supply voltage. Different load conditions change the ability of the amplifier to swing close to the rails.

8.3.3 Packages with an Exposed Thermal Pad

The TSV91x family is available in packages such as the WSON-8 (DSG) which feature an exposed thermal pad. Inside the package, the die is attached to this thermal pad using an electrically conductive compound. For this reason, when using a package with an exposed thermal pad, the thermal pad must either be connected to V- or left floating. Attaching the thermal pad to a potential other then V- is not allowed, and the performance of the device is not assured when doing so.

8.3.4 Overload Recovery

Overload recovery is defined as the time required for the operational amplifier output to recover from a saturated state to a linear state. The output devices of the operational amplifier enter a saturation region when the output voltage exceeds the rated operating voltage, because of the high input voltage or the high gain. After the device enters the saturation region, the charge carriers in the output devices require time to return to the linear state. After the charge carriers return to the linear state, the device begins to slew at the specified slew rate. Therefore, the propagation delay (in case of an overload condition) is the sum of the overload recovery time and the slew time. The overload recovery time for the TSV91x series is approximately 200 ns.

8.4 Device Functional Modes

The TSV91x family has a single functional mode. These devices are powered on as long as the power-supply voltage is between 2.5 V (\pm 1.25 V) and 5.5 V (\pm 2.75 V).



9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The TSV91x series features 8-MHz bandwidth and 4.5-V/ μ s slew rate with only 550 μ A of supply current per channel, providing good AC performance at low power consumption. DC applications are well served with a low input noise voltage of 18 nV / $\sqrt{\text{Hz}}$ at 1 kHz, low input bias current, and a typical input offset voltage of 0.3 mV.

9.2 Typical Application

Figure 35 shows the TSV91x configured in a low-side, motor-control application.

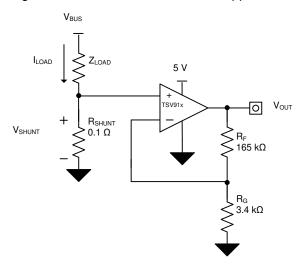


Figure 35. TSV91x in a Low-Side, Motor-Control Application

9.2.1 Design Requirements

The design requirements for this design are:

Load current: 0 A to 1 AOutput voltage: 4.95 V

Maximum shunt voltage: 100 mV

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Typical Application (continued)

9.2.2 Detailed Design Procedure

The transfer function of the circuit in Figure 35 is shown in Equation 1.

$$V_{OUT} = I_{LOAD} \times R_{SHUNT} \times Gain$$
 (1)

The load current (I_{LOAD}) produces a voltage drop across the shunt resistor (R_{SHUNT}). The load current is set from 0 A to 1 A. To keep the shunt voltage below 100 mV at maximum load current, the largest shunt resistor is defined using Equation 2.

$$R_{SHUNT} = \frac{V_{SHUNT_MAX}}{I_{LOAD_MAX}} = \frac{100mV}{1A} = 100m\Omega$$
(2)

Using Equation 2, R_{SHUNT} is 100 m Ω . The voltage drop produced by I_{LOAD} and R_{SHUNT} is amplified by the TSV91x to produce an output voltage of approximately 0 V to 4.95 V. The gain required by the TSV91x to produce the necessary output voltage is calculated using Equation 3:

$$Gain = \frac{\left(V_{OUT_MAX} - V_{OUT_MIN}\right)}{\left(V_{IN_MAX} - V_{IN_MIN}\right)}$$
(3)

Using Equation 3, the required gain is calculated to be 49.5 V/V, which is set with resistors R_F and R_G . Equation 4 is used to size the resistors, R_F and R_G , to set the gain of the TSV91x to 49.5 V/V.

$$Gain = 1 + \frac{(R_F)}{(R_G)}$$
(4)

Selecting R_F as 165 $k\Omega$ and R_G as 3.4 $k\Omega$ provides a combination that equals roughly 49.5 V/V. Figure 36 shows the measured transfer function of the circuit shown in Figure 35.

9.2.3 Application Curve

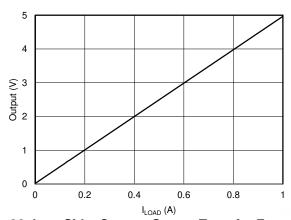


Figure 36. Low-Side, Current-Sense, Transfer Function



10 Power Supply Recommendations

The TSV91x series is specified for operation from 2.5 V to 5.5 V (±1.25 V to ±2.75 V); many specifications apply from -40°C to 125°C. The Typical Characteristics section presents parameters that can exhibit significant variance with regard to operating voltage or temperature.

CAUTION

Supply voltages larger than 6 V can permanently damage the device; see the Absolute Maximum Ratings table.

Place 0.1-µF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or highimpedance power supplies. For more detailed information on bypass capacitor placement, see the Layout Example section.

10.1 Input and ESD Protection

The TSV91x series incorporates internal ESD protection circuits on all pins. For input and output pins, this protection consists of current-steering diodes connected between the input and power-supply pins. These ESD protection diodes provide in-circuit, input overdrive protection, as long as the current is limited to 10-mA, as stated in the Absolute Maximum Ratings table. Figure 37 shows how a series input resistor is added to the driven input to limit the input current. The added resistor contributes thermal noise at the amplifier input and the value must be kept to a minimum in noise-sensitive applications.

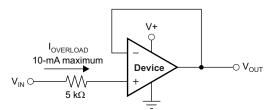


Figure 37. Input Current Protection

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11 Layout

11.1 Layout Guidelines

For best operational performance of the device, use good printed-circuit board (PCB) layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole and of op amp itself. Bypass capacitors are used to reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
 - Connect low-ESR, 0.1-µF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for singlesupply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most-effective
 methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground
 planes. A ground plane helps distribute heat and reduces electromagnetic interference (EMI) noise
 pickup. Make sure to physically separate digital and analog grounds, paying attention to the flow of the
 ground current. For more detailed information, see Circuit Board Layout Techniques.
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If these traces cannot be kept separate, crossing the sensitive trace perpendicular is much better as opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible. As shown in Figure 39, keeping RF and RG close to the inverting input minimizes parasitic capacitance on the inverting input.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.
- Cleaning the PCB following board assembly is recommended for best performance.
- Any precision integrated circuit can experience performance shifts resulting from moisture ingress into the
 plastic package. Following any aqueous PCB cleaning process, baking the PCB assembly is
 recommended to remove moisture introduced into the device packaging during the cleaning process. A
 low-temperature, post-cleaning bake at 85°C for 30 minutes is sufficient for most circumstances.

11.2 Layout Example

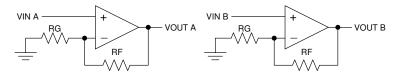


Figure 38. Schematic Representation for Figure 39

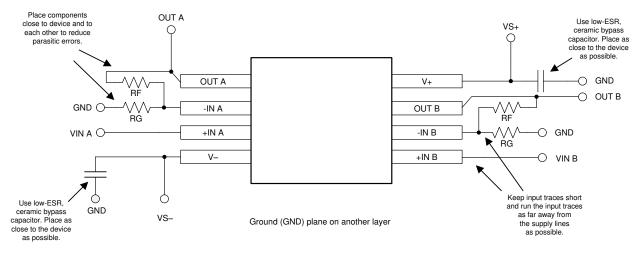


Figure 39. Layout Example

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12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

Texas Instruments, Circuit Board Layout Techniques, SLOA089

12.2 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to order now.

Table 1. Related Links

PARTS	PRODUCT FOLDER	PRODUCT FOLDER ORDER NOW		TOOLS & SOFTWARE	SUPPORT & COMMUNITY
TSV911	Click here	Click here	Click here	Click here	Click here
TSV912	Click here	Click here	Click here	Click here	Click here
TSV914	Click here	Click here	Click here	Click here	Click here

12.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.4 Community Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

12.5 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

12.6 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.7 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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2-Dec-2025

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
TSV911AIDBVR	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	1U2F
TSV911AIDBVR.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1U2F
TSV911AIDBVRG4	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1U2F
TSV911AIDBVRG4.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1U2F
TSV911AIDCKR	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	SN	Level-2-260C-1 YEAR	-40 to 125	1EK
TSV911AIDCKR.A	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	SN	Level-2-260C-1 YEAR	-40 to 125	1EK
TSV912AIDDFR	Active	Production	SOT-23-THIN (DDF) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T12A
TSV912AIDDFR.A	Active	Production	SOT-23-THIN (DDF) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T12A
TSV912AIDDFRG4	Active	Production	SOT-23-THIN (DDF) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T12A
TSV912AIDDFRG4.A	Active	Production	SOT-23-THIN (DDF) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T12A
TSV912AIDGKR	Active	Production	VSSOP (DGK) 8	2500 LARGE T&R	Yes	NIPDAU SN NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	T912
TSV912AIDGKR.A	Active	Production	VSSOP (DGK) 8	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	T912
TSV912AIDGKT	Active	Production	VSSOP (DGK) 8	250 SMALL T&R	Yes	NIPDAU SN NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	T912
TSV912AIDGKT.A	Active	Production	VSSOP (DGK) 8	250 SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	T912
TSV912AIDR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TSV912
TSV912AIDR.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TSV912
TSV912AIDRG4	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TSV912
TSV912AIDRG4.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TSV912
TSV912AIDSGR	Active	Production	WSON (DSG) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T912
TSV912AIDSGR.A	Active	Production	WSON (DSG) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T912
TSV912AIDSGT	Active	Production	WSON (DSG) 8	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T912
TSV912AIDSGT.A	Active	Production	WSON (DSG) 8	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T912
TSV912AIPWR	Active	Production	TSSOP (PW) 8	2000 LARGE T&R	Yes	NIPDAU SN	Level-2-260C-1 YEAR	-40 to 125	TSV912
TSV912AIPWR.A	Active	Production	TSSOP (PW) 8	2000 LARGE T&R	Yes	SN	Level-2-260C-1 YEAR	-40 to 125	TSV912
TSV914AIDR	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TSV914AD
TSV914AIDR.A	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TSV914AD
TSV914AIDRG4	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TSV914AD
TSV914AIDRG4.A	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TSV914AD



-40 to 125

2-Dec-2025

TSV914



TSV914AIPWT.A

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Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/	MSL rating/	Op temp (°C)	Part marking
	(1)	(2)			(3)	Ball material	Peak reflow		(6)
						(4)	(5)		
TSV914AIPWR	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU SN	Level-2-260C-1 YEAR	-40 to 125	TSV914
TSV914AIPWR.A	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	SN	Level-2-260C-1 YEAR	-40 to 125	TSV914
TSV914AIPWT	Active	Production	TSSOP (PW) 14	250 SMALL T&R	Yes	NIPDAU I SN	Level-2-260C-1 YEAR	-40 to 125	TSV914

Yes

250 | SMALL T&R

SN

Level-2-260C-1 YEAR

Active

Production

TSSOP (PW) | 14

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

⁽¹⁾ Status: For more details on status, see our product life cycle.

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

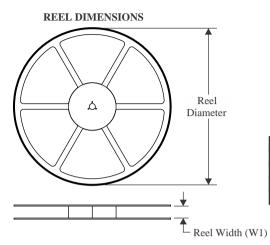
⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

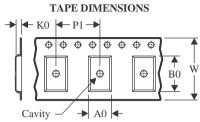
⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.



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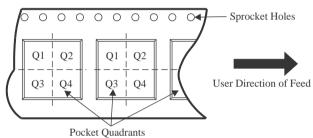
TAPE AND REEL INFORMATION





Γ	A0	Dimension designed to accommodate the component width
	В0	Dimension designed to accommodate the component length
	K0	Dimension designed to accommodate the component thickness
	W	Overall width of the carrier tape
	P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TSV911AIDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TSV911AIDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TSV911AIDBVRG4	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TSV911AIDCKR	SC70	DCK	5	3000	180.0	8.4	2.3	2.5	1.2	4.0	8.0	Q3
TSV912AIDDFR	SOT-23- THIN	DDF	8	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TSV912AIDDFRG4	SOT-23- THIN	DDF	8	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TSV912AIDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TSV912AIDGKT	VSSOP	DGK	8	250	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TSV912AIDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TSV912AIDRG4	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TSV912AIDSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TSV912AIDSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TSV912AIPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
TSV914AIDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TSV914AIDRG4	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1



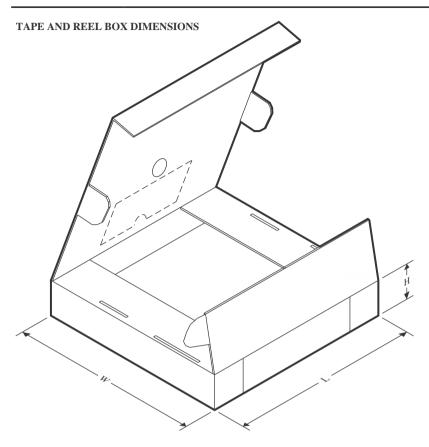
PACKAGE MATERIALS INFORMATION

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Device		Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TSV914AIPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TSV914AIPWT	TSSOP	PW	14	250	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1



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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TSV911AIDBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
TSV911AIDBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
TSV911AIDBVRG4	SOT-23	DBV	5	3000	210.0	185.0	35.0
TSV911AIDCKR	SC70	DCK	5	3000	210.0	185.0	35.0
TSV912AIDDFR	SOT-23-THIN	DDF	8	3000	210.0	185.0	35.0
TSV912AIDDFRG4	SOT-23-THIN	DDF	8	3000	210.0	185.0	35.0
TSV912AIDGKR	VSSOP	DGK	8	2500	353.0	353.0	32.0
TSV912AIDGKT	VSSOP	DGK	8	250	353.0	353.0	32.0
TSV912AIDR	SOIC	D	8	2500	353.0	353.0	32.0
TSV912AIDRG4	SOIC	D	8	2500	353.0	353.0	32.0
TSV912AIDSGR	WSON	DSG	8	3000	210.0	185.0	35.0
TSV912AIDSGT	WSON	DSG	8	250	210.0	185.0	35.0
TSV912AIPWR	TSSOP	PW	8	2000	353.0	353.0	32.0
TSV914AIDR	SOIC	D	14	2500	353.0	353.0	32.0
TSV914AIDRG4	SOIC	D	14	2500	353.0	353.0	32.0
TSV914AIPWR	TSSOP	PW	14	2000	353.0	353.0	32.0
TSV914AIPWT	TSSOP	PW	14	250	353.0	353.0	32.0



SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





SMALL OUTLINE PACKAGE



NOTES:

PowerPAD is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-187.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
- 8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
- 9. Size of metal pad may vary due to creepage requirement.



SMALL OUTLINE PACKAGE



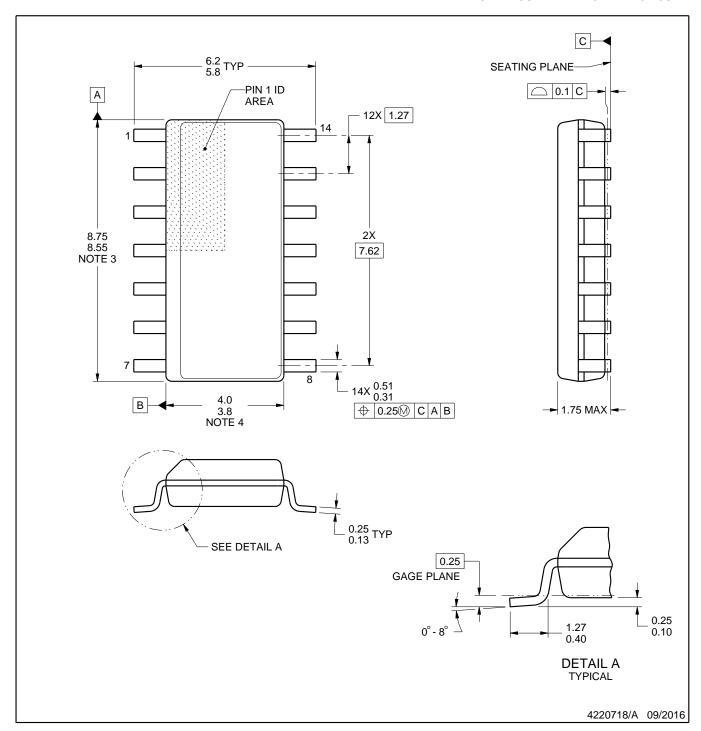
NOTES: (continued)

- 11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 12. Board assembly site may have different recommendations for stencil design.





SMALL OUTLINE INTEGRATED CIRCUIT



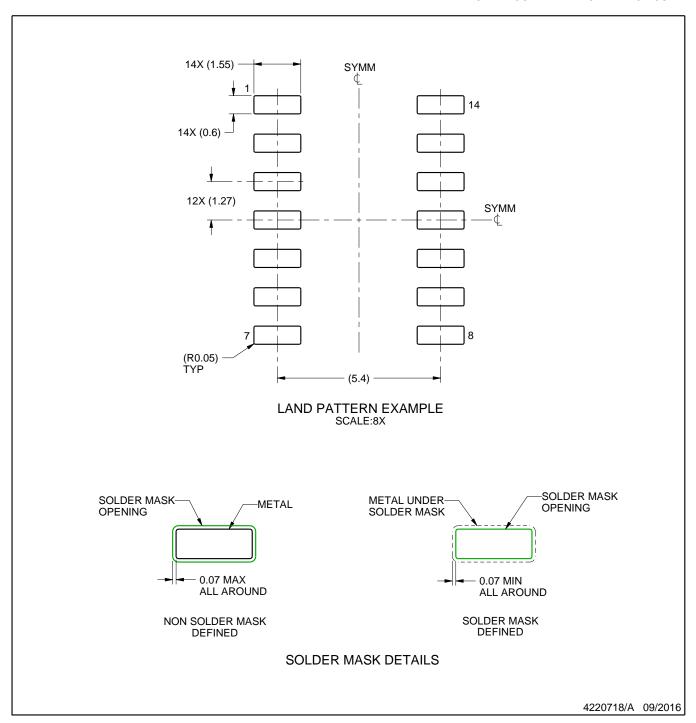
NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
- 5. Reference JEDEC registration MS-012, variation AB.



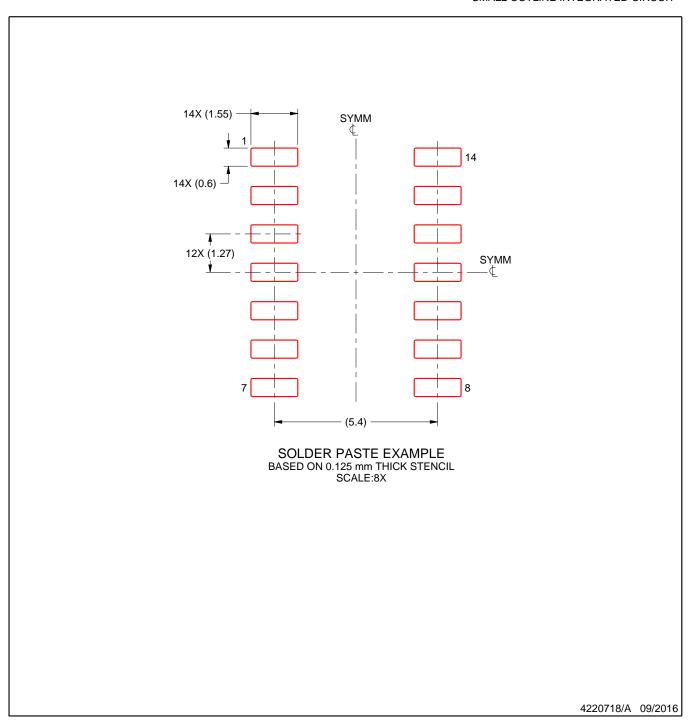


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



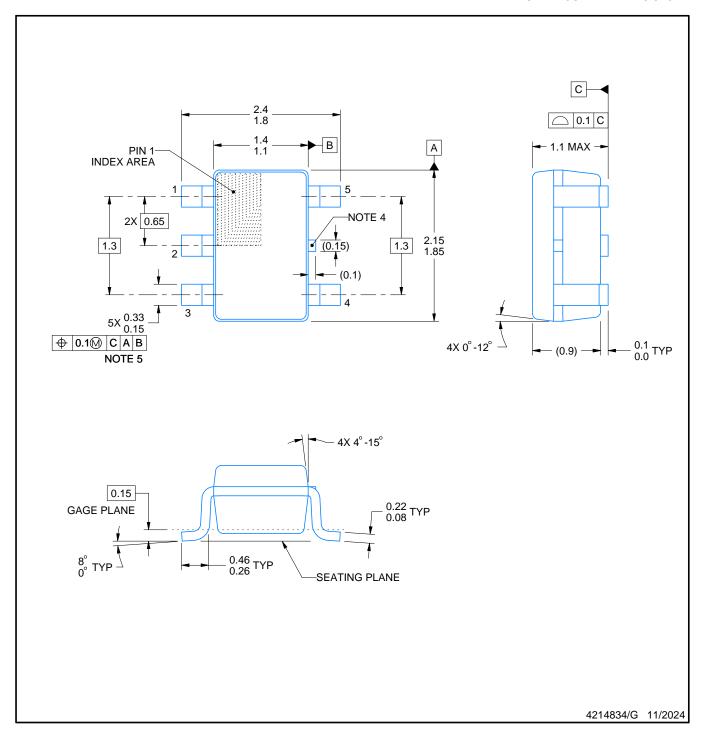


- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





SMALL OUTLINE TRANSISTOR

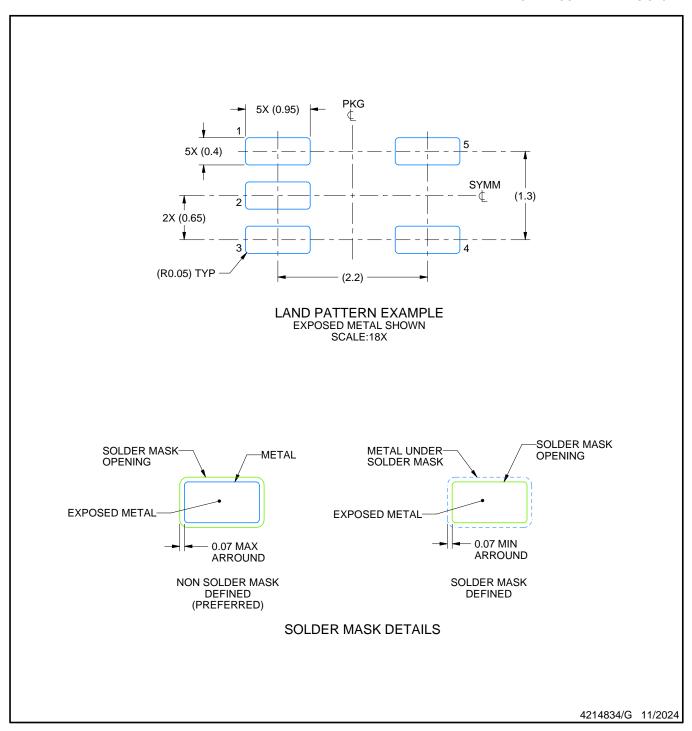


- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-203.

- 4. Support pin may differ or may not be present.5. Lead width does not comply with JEDEC.
- 6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side



SMALL OUTLINE TRANSISTOR

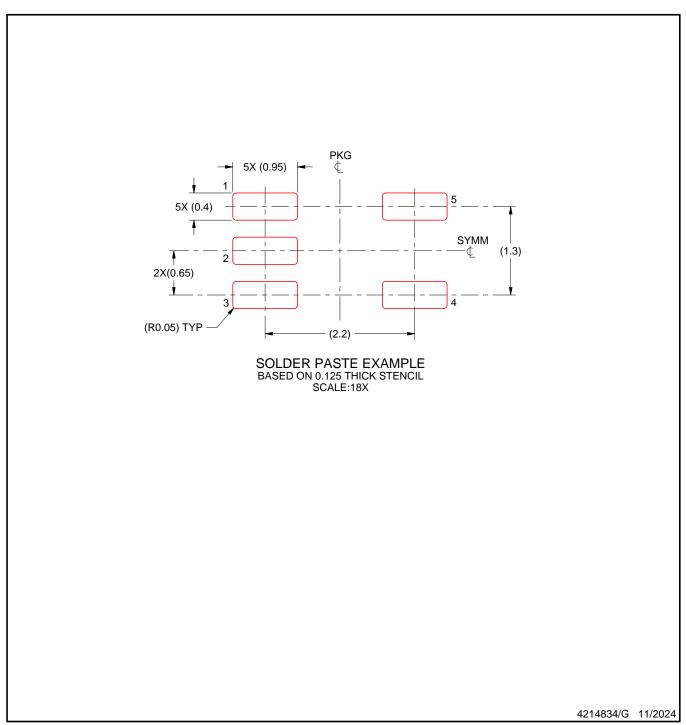


NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR

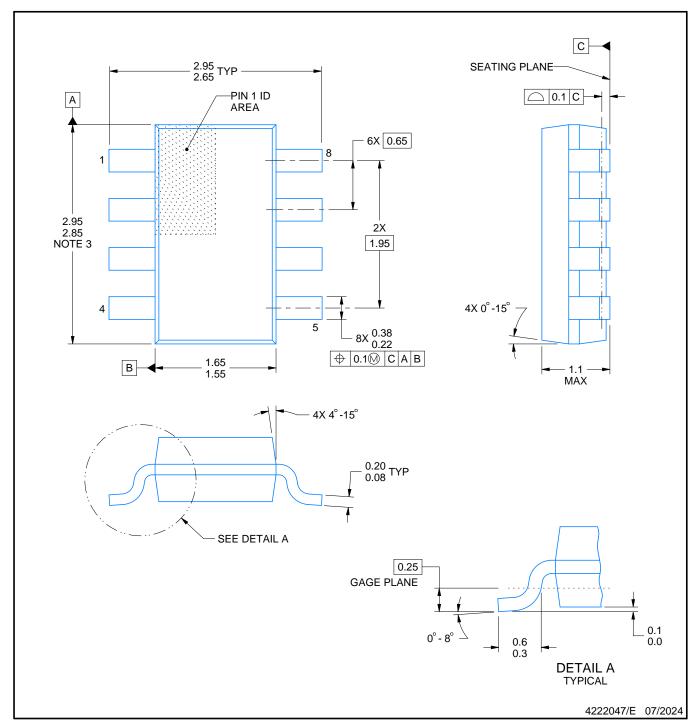


- 9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 10. Board assembly site may have different recommendations for stencil design.





PLASTIC SMALL OUTLINE



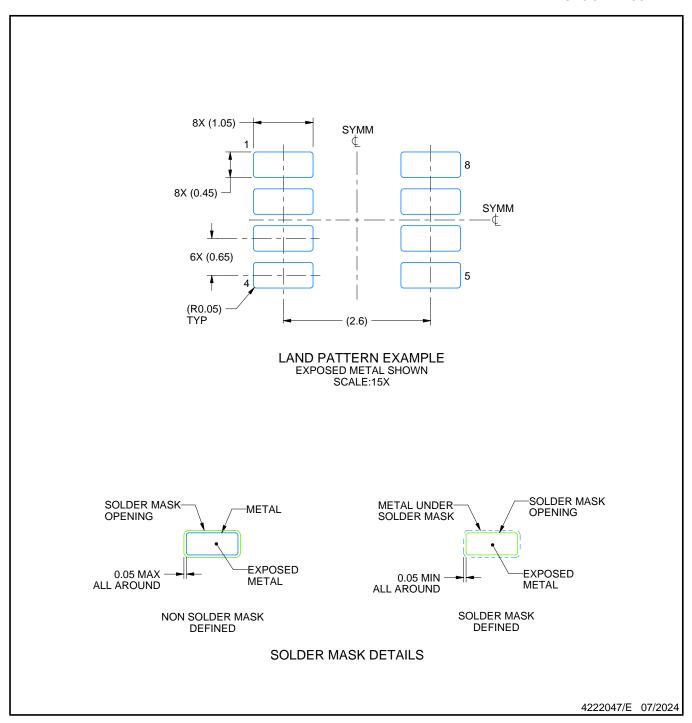
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.



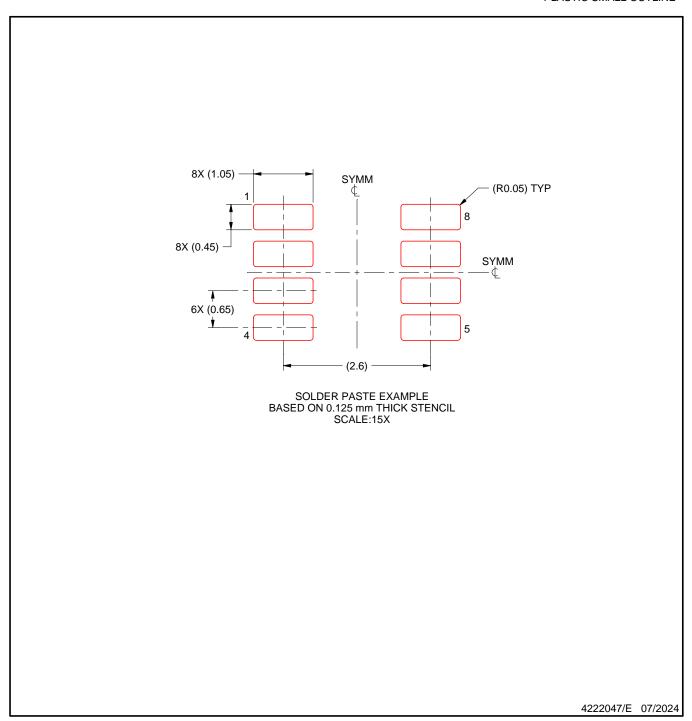
PLASTIC SMALL OUTLINE



- 4. Publication IPC-7351 may have alternate designs.
- 5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



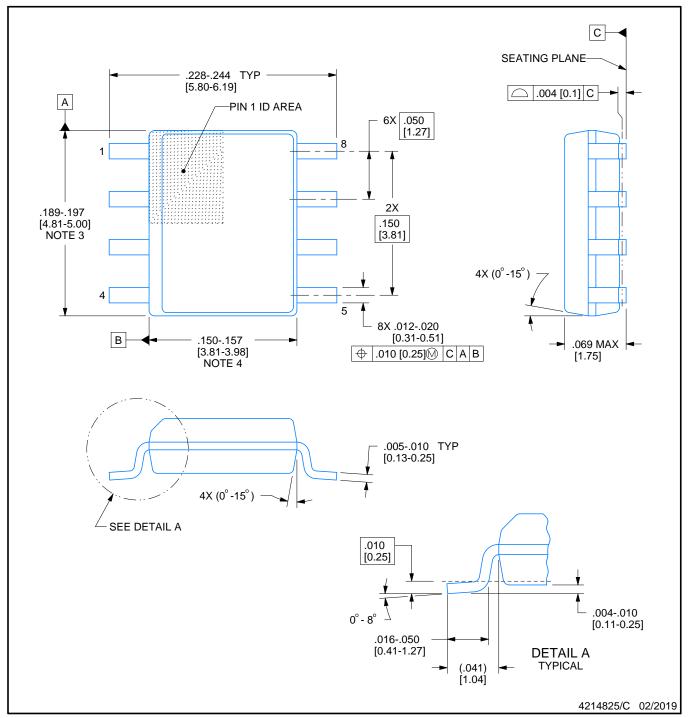
PLASTIC SMALL OUTLINE



- 6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 7. Board assembly site may have different recommendations for stencil design.

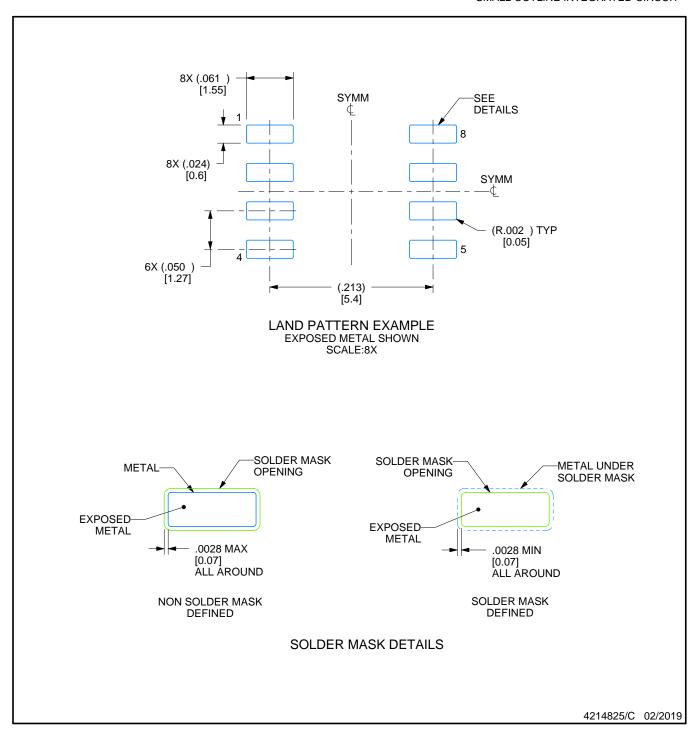






- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



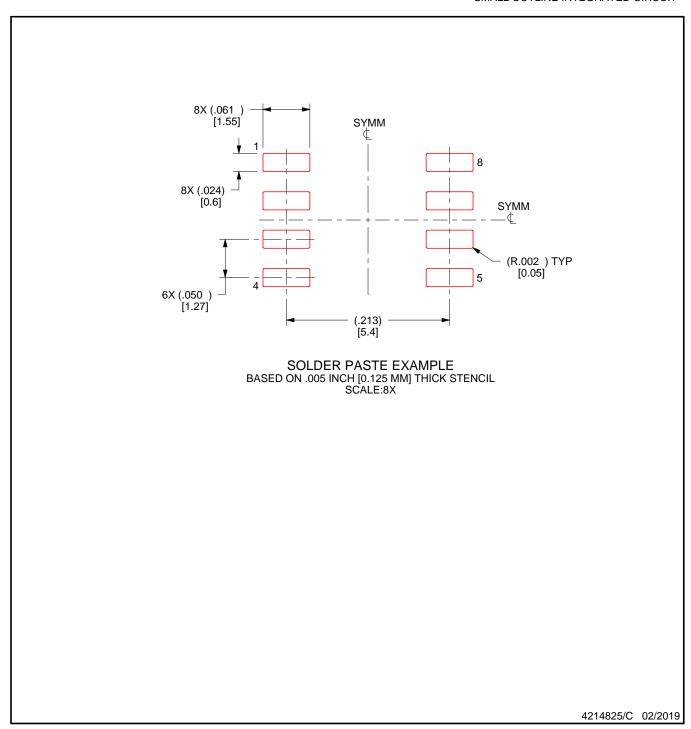


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





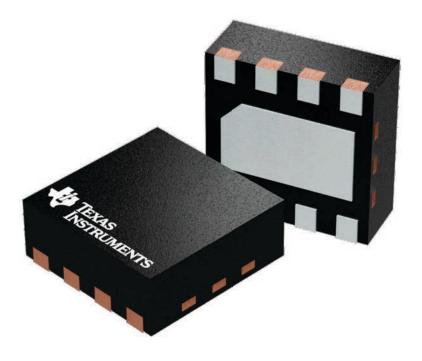
- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



2 x 2, 0.5 mm pitch

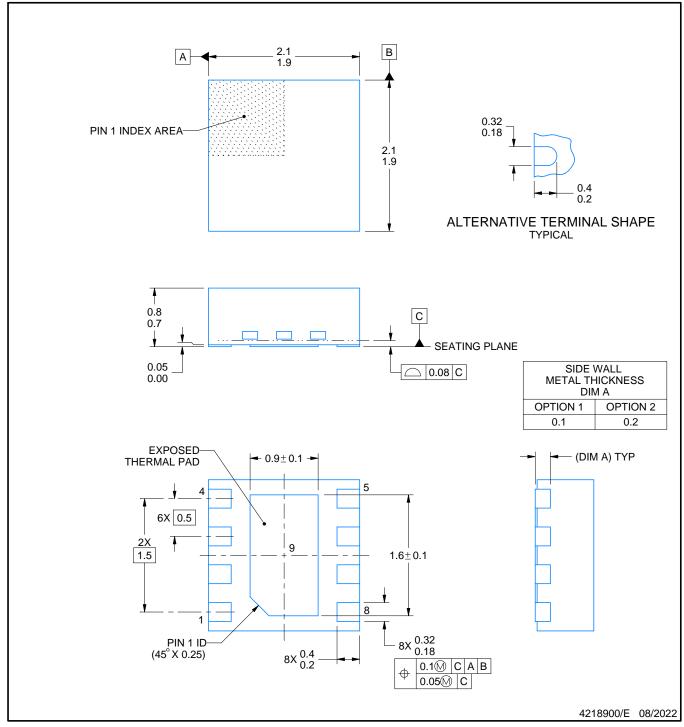
PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





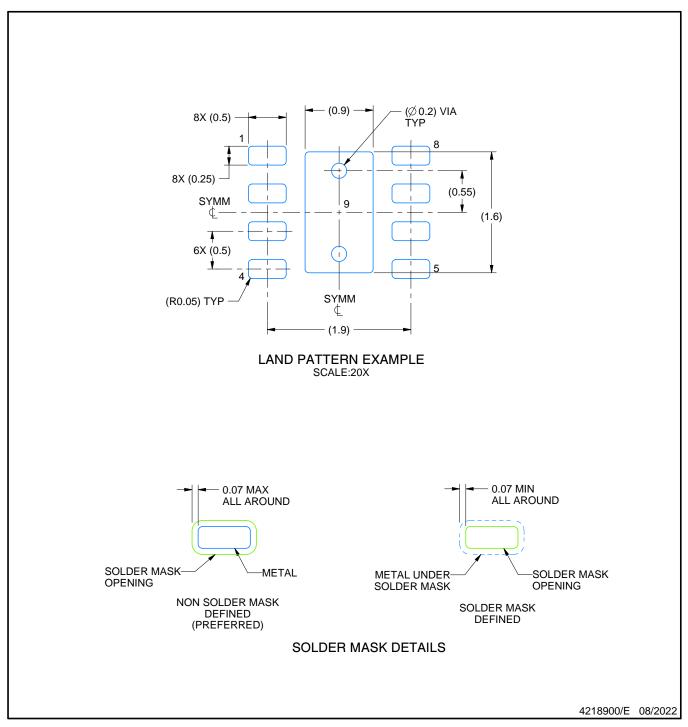
PLASTIC SMALL OUTLINE - NO LEAD



- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



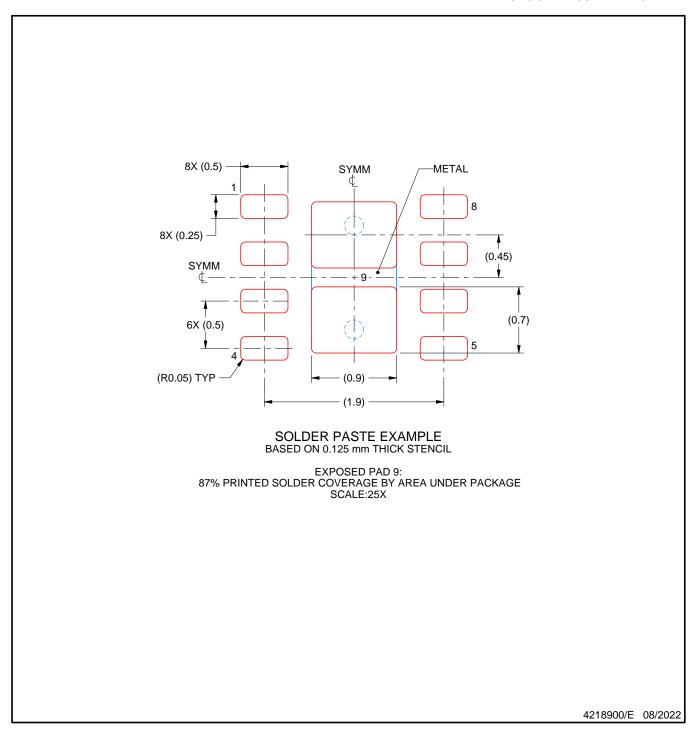
PLASTIC SMALL OUTLINE - NO LEAD



- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC SMALL OUTLINE - NO LEAD

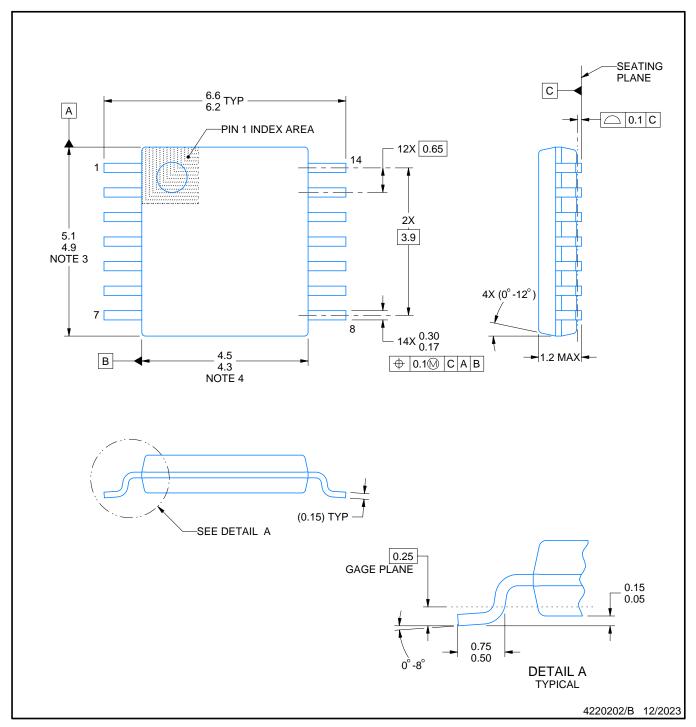


NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.





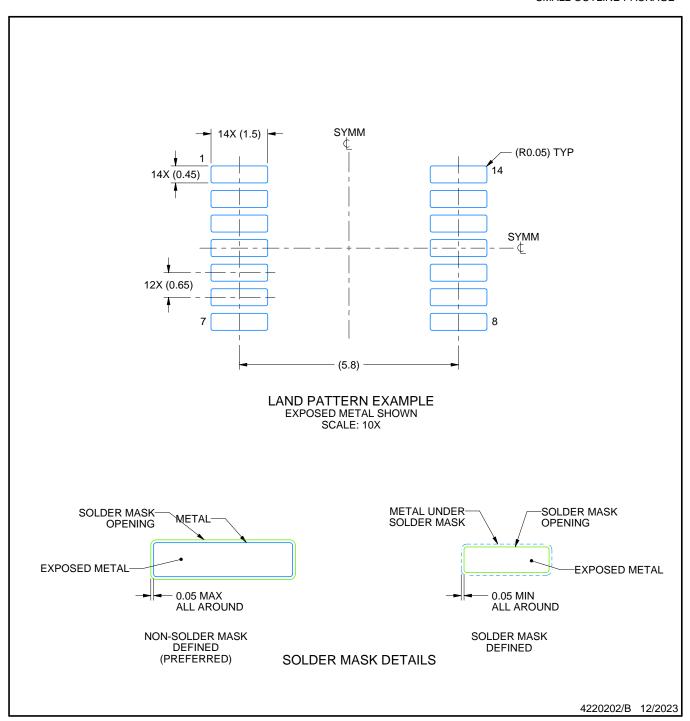


- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



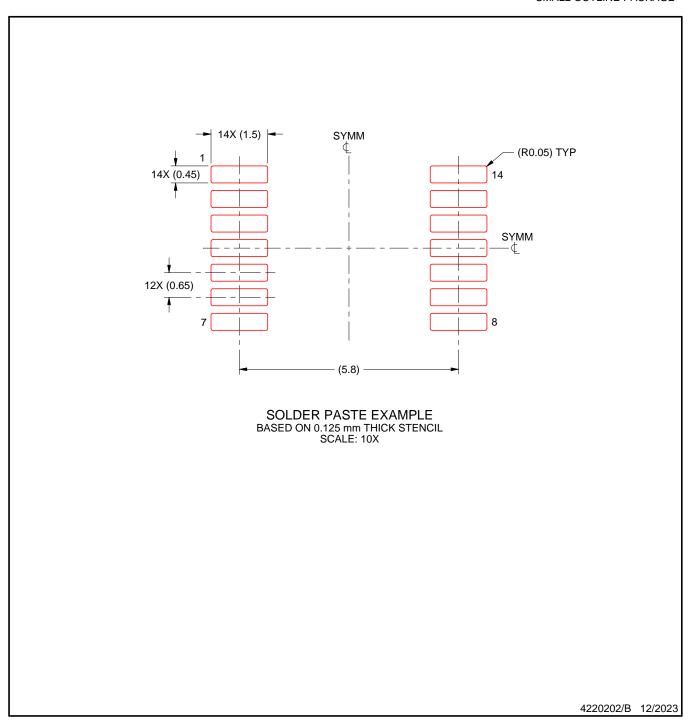


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

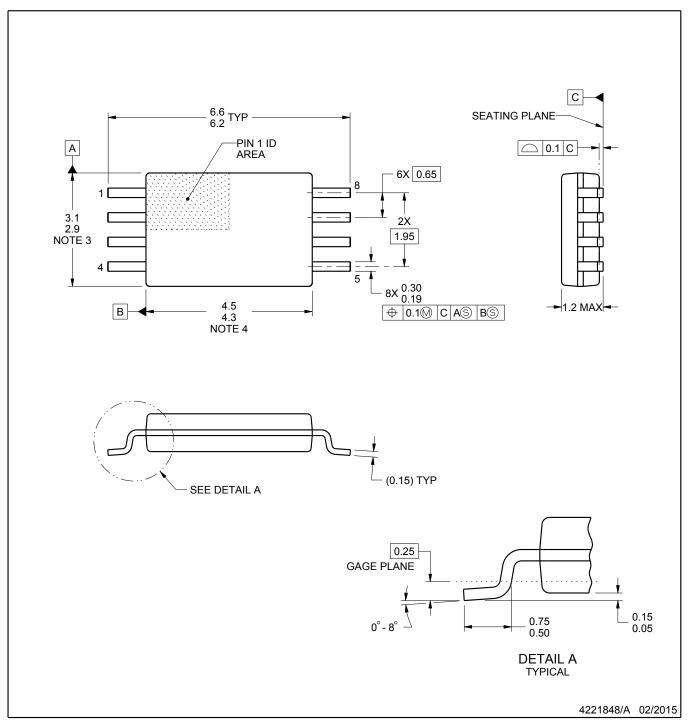




- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





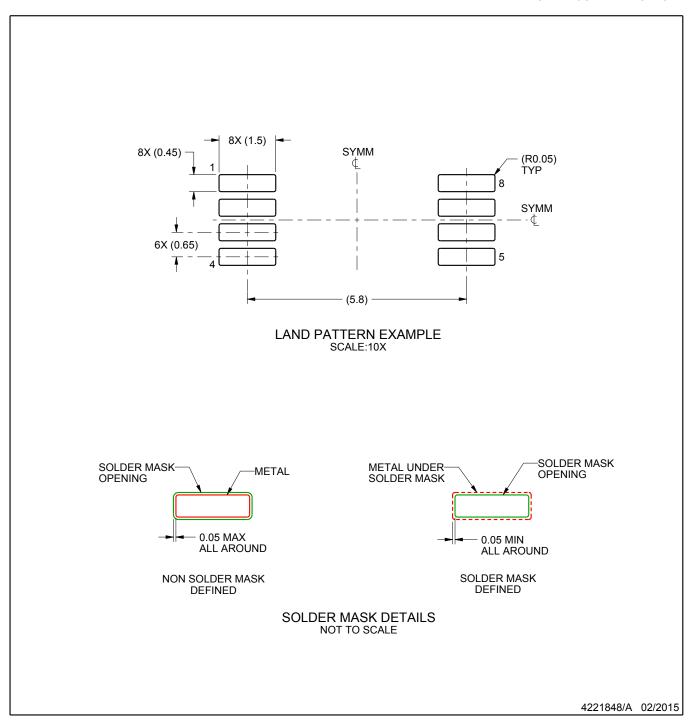


- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153, variation AA.



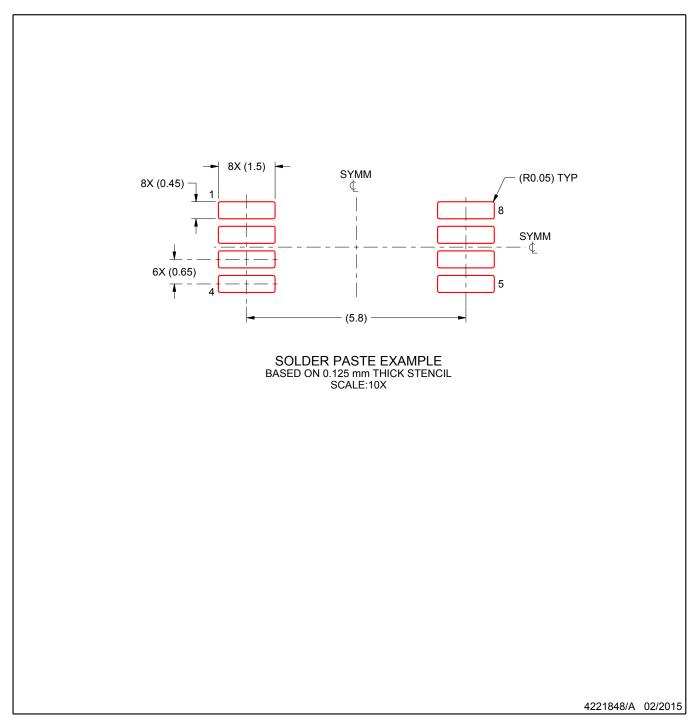


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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